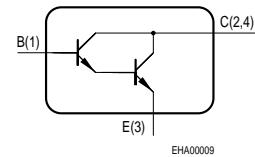
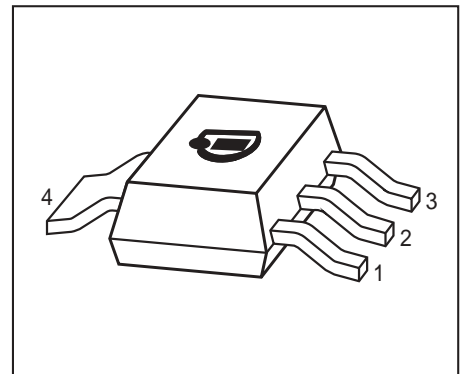


NPN Silicon Darlington Transistors

- For general AF applications
- High collector current
- High current gain
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101



Type	Marking	Pin Configuration				Package
		1 = B	2 = C	3 = E	4 = C	
BCP49	BCP 49	1 = B	2 = C	3 = E	4 = C	SOT223

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CEO}	60	V
Collector-base voltage	V_{CBO}	80	
Emitter-base voltage	V_{EBO}	10	
DC collector current	I_C	500	mA
Peak collector current	I_{CM}	800	
Base current	I_B	100	
Peak base current	I_{BM}	200	W
Total power dissipation, $T_S = 124\text{ °C}$	P_{tot}	1.5	
Junction temperature	T_j	150	
Storage temperature	T_{stg}	-65 ... 150	°C

Thermal Resistance

Junction - soldering point ²⁾	R_{thJS}	≤17	K/W
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¹Pb-containing package may be available upon special request

²For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	60	-	-	V
Collector-base breakdown voltage $I_C = 100\text{ }\mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	80	-	-	
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	10	-	-	
Collector cutoff current $V_{CB} = 60\text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Collector cutoff current $V_{CB} = 60\text{ V}, I_E = 0, T_A = 150\text{ }^\circ\text{C}$	I_{CBO}	-	-	10	μA
Emitter cutoff current $V_{EB} = 5\text{ V}, I_C = 0$	I_{EBO}	-	-	100	nA
DC current gain 1) $I_C = 100\text{ }\mu\text{A}, V_{CE} = 1\text{ V}$	h_{FE}	2000	-	-	-
DC current gain 1) $I_C = 10\text{ mA}, V_{CE} = 5\text{ V}$	h_{FE}	4000	-	-	
DC current gain 1) $I_C = 100\text{ mA}, V_{CE} = 5\text{ V}$	h_{FE}	10000	-	-	
DC current gain 1) $I_C = 500\text{ mA}, V_{CE} = 5\text{ V}$	h_{FE}	2000	-	-	

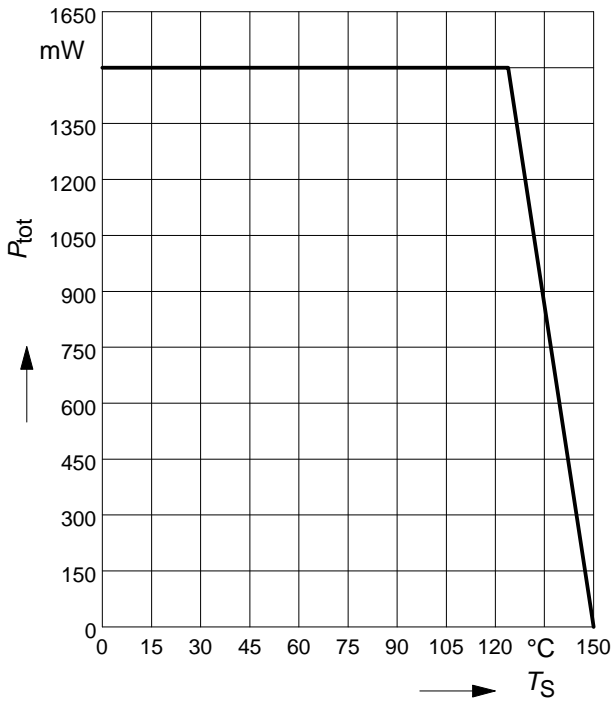
 1) Pulse test: $t \leq 300\text{ }\mu\text{s}$, $D = 2\%$

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter saturation voltage ¹⁾ $I_C = 100\text{ mA}, I_B = 0.1\text{ mA}$	V_{CEsat}	-	-	1	V
Base-emitter saturation voltage 1) $I_C = 100\text{ mA}, I_B = 0.1\text{ mA}$	V_{BEsat}	-	-	1.5	
AC Characteristics					
Transition frequency $I_C = 50\text{ mA}, V_{CE} = 5\text{ V}, f = 100\text{ MHz}$	f_T	-	200	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}, f = 1\text{ MHz}$	C_{cb}	-	6.5	-	pF

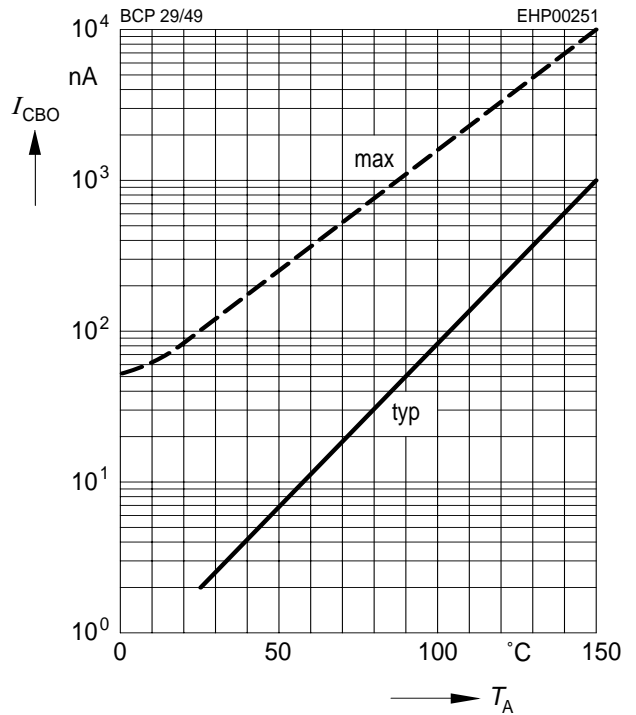
1) Pulse test: $t \leq 300\mu\text{s}$, $D = 2\%$

Total power dissipation $P_{tot} = f(T_S)$



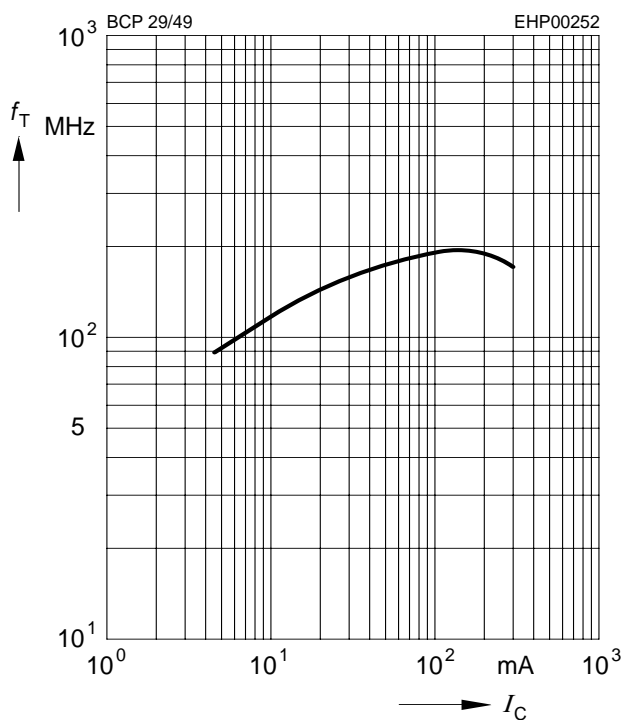
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CB} = V_{CEmax}$



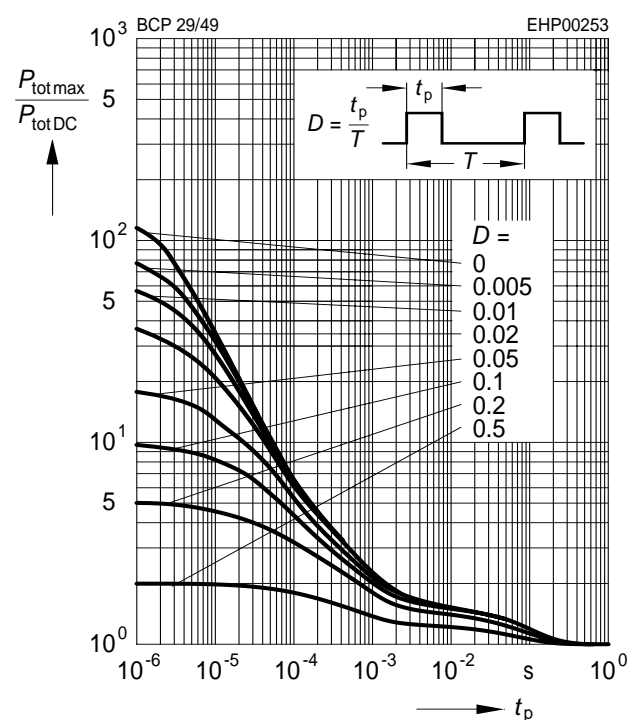
Transition frequency $f_T = f(I_C)$

$V_{CE} = 5V$



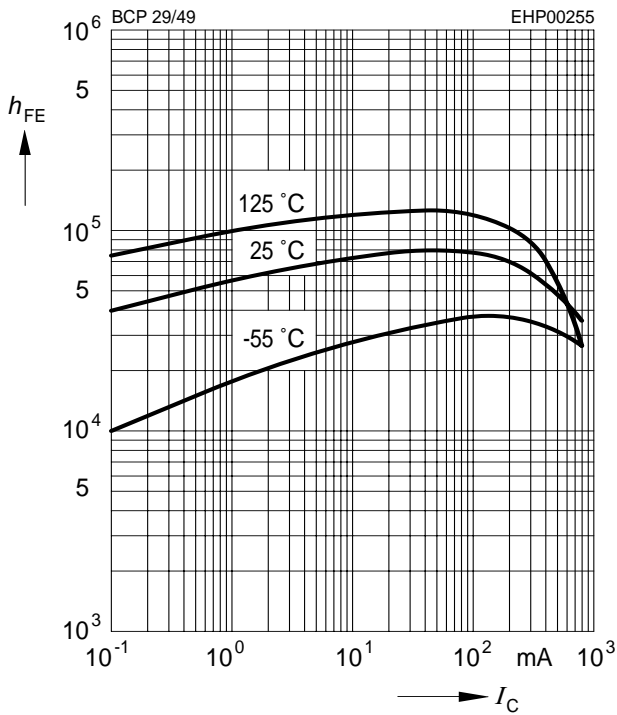
Permissible pulse load

$P_{totmax} / P_{totDC} = f(t_p)$



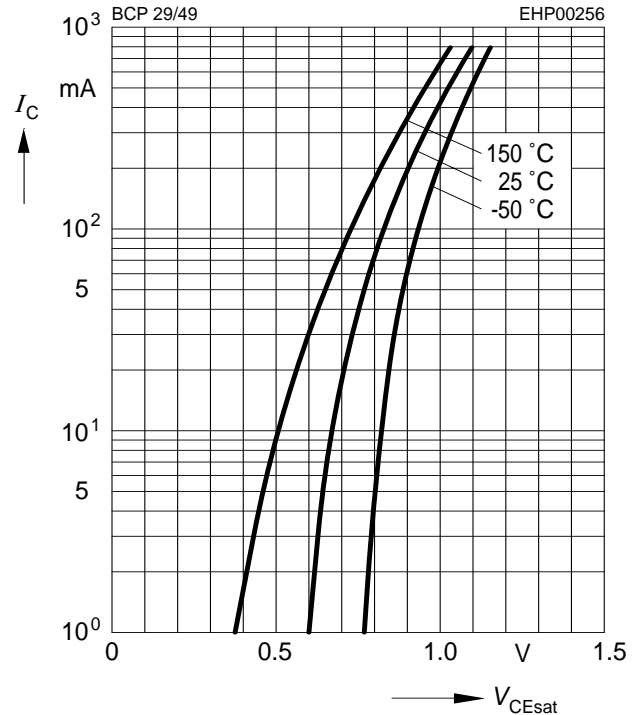
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5V$



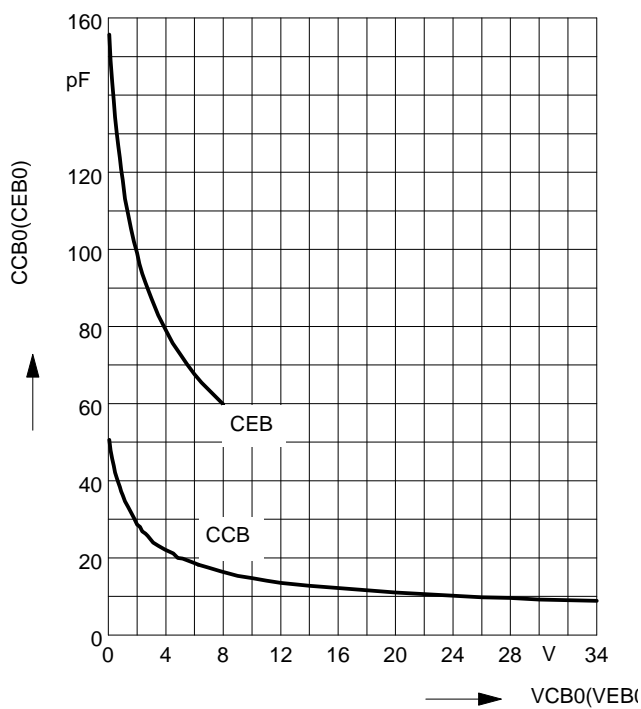
Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 1000$



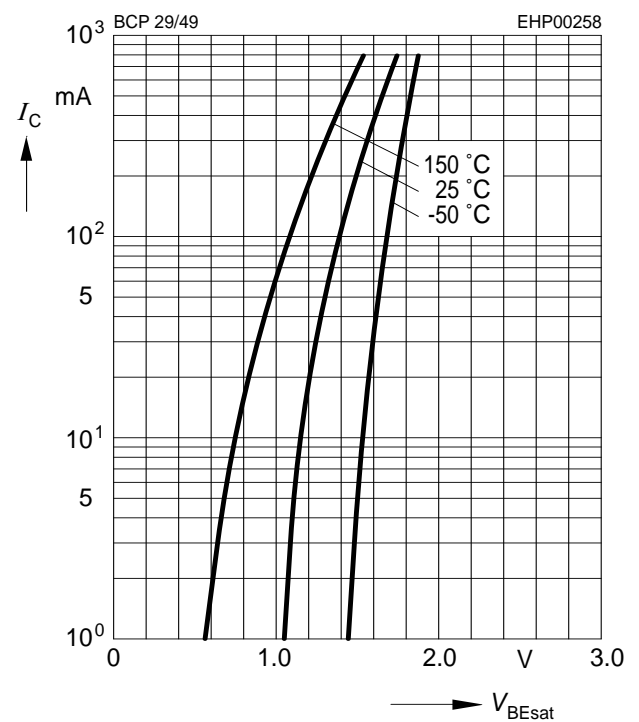
Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$

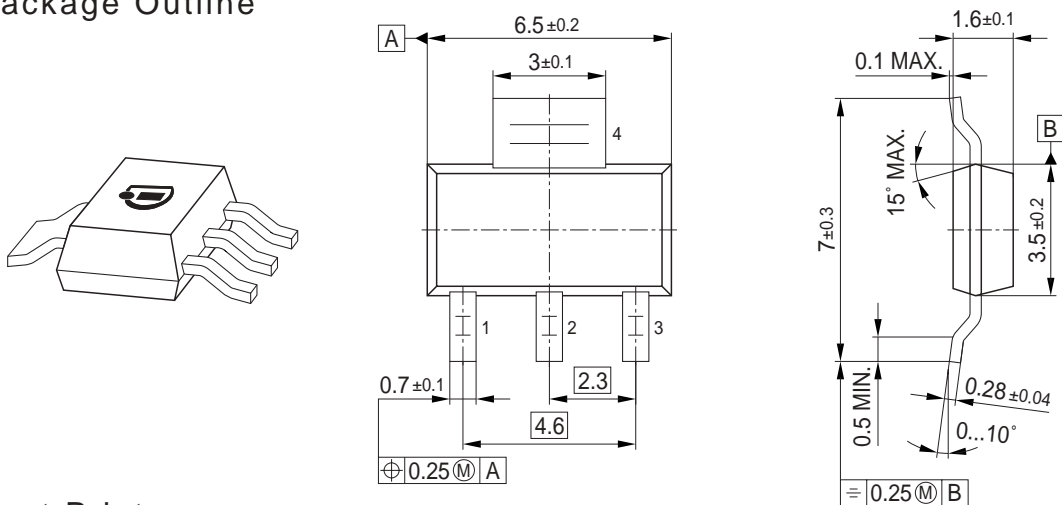


Base-emitter saturation voltage

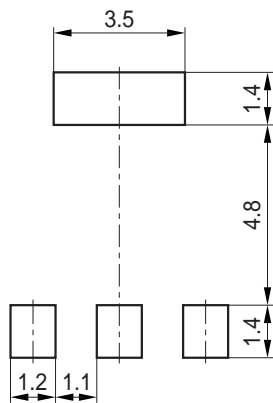
$I_C = f(V_{BEsat}), h_{FE} = 1000$



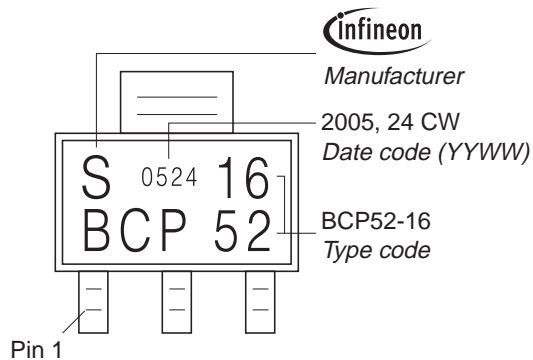
Package Outline



Foot Print

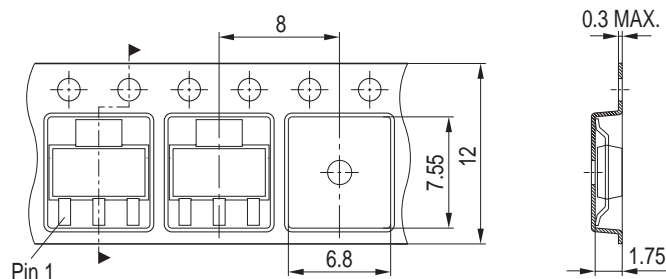


Marking Layout (Example)



Packing

Reel ø180 mm = 1.000 Pieces/Reel
 Reel ø330 mm = 4.000 Pieces/Reel



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